

# Update to Single Event Metadata Analysis Activities at JPL

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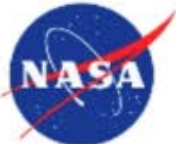
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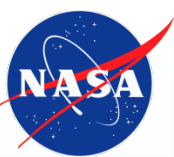
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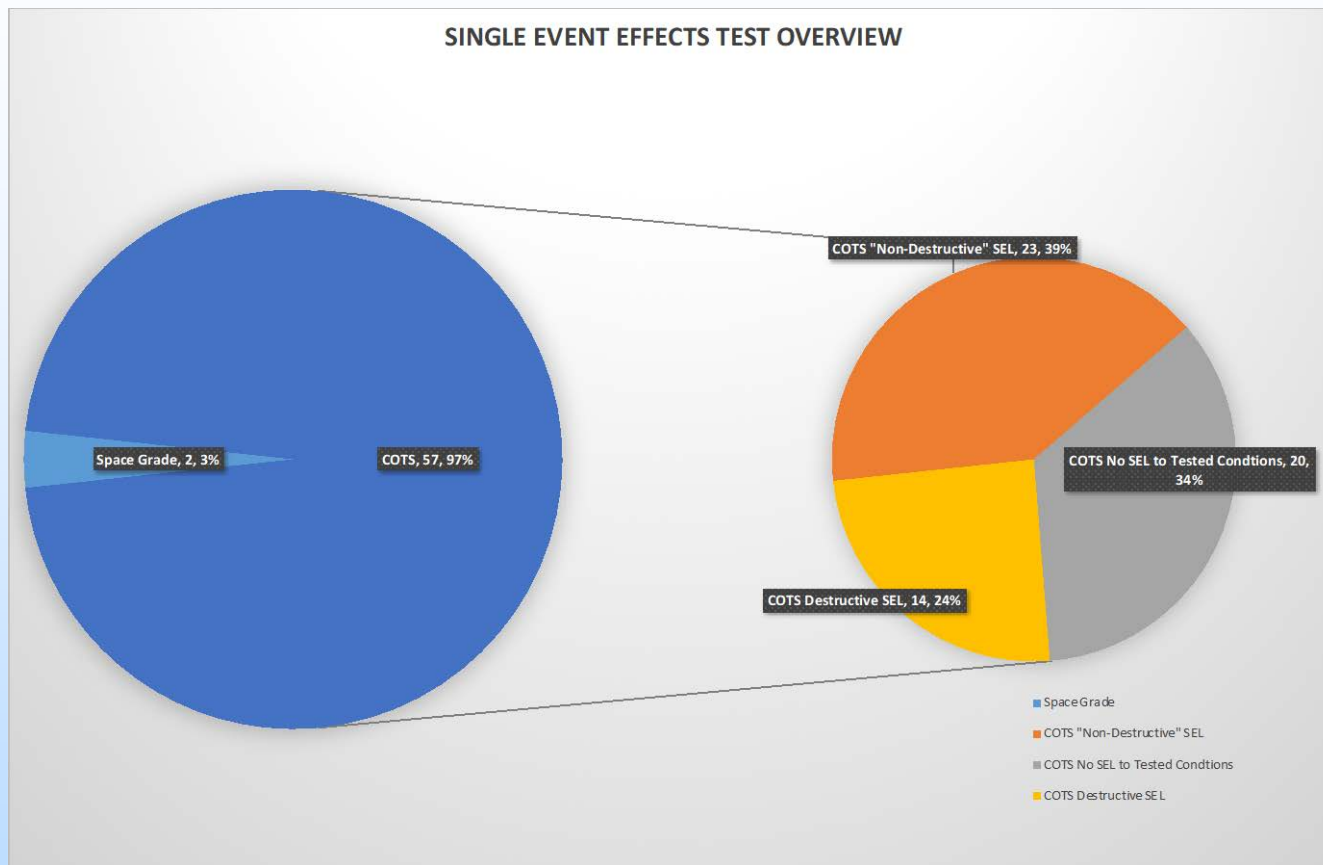


# NEPP - Charter





# Background





# Task Objectives

- Due to the paradigm shift in spacecraft technology utilization, and the shift towards COTS technology, a plethora of COTS-based devices have been tested in recent years in addition to the decades of radiation data available in literature and online databases.
- We are developing an agency-level available database that attempts to expose radiation trends in the metadata.
- Our original focus will be on destructive effects (SEL, SEGR, etc.), but we will look beyond the standard voltage and temperature trends to manufacturer, technology process (not just node), device variables (e.g. for ADCs: number of bits, speed, architecture, etc).
- End goal is to expose buried trends to aid in part selection and MBSE analysis and guide bounding methodologies



# Approach

- **Assemble database of radiation results for a single part type**
- **Focus on one radiation effect (SEL screening)**
- **Use data scraping to automate database population of device parameters**
- **Employ predictive model for untested parts**
- **Employ machine learning to discover hidden trends**



# Previous Work - Example of Output from Model V.2.0



## Radiation Metadata Tool

This tool is for the collection of testing data related to CMOS electrical components as well as assessing the risk associated with components for Single Event Latchup (SEL).

Risk Profiling Data Collection

### Risk Profiling

Input a part number to see the risk associated with a SEL at different LETs. If we do not currently have the part number, in our records, we will go out and scrape the internet for the metadata, save it for future use, then make our predictions based on what we found.

Clear

### IEEE Part Info

Mfr Package Description	0.209 INCH, PLASTIC, SSOP-28
REACH Compliant	Yes
Status	Active
Converter Type	ADC, SUCCESSIVE APPROXIMATION
Analog Input Voltage-Min	-2.5 V
Analog Input Voltage-Max	2.5 V
Conversion Time-Max	1.15 $\mu$ s
JESD-30 Code	R-PDSO-G28
JESD-609 Code	e0
Linearity Error-Max (EL)	0.0122 %
Moisture Sensitivity Level	1
Negative Supply Voltage-Nom	-5.0 V
Number of Analog In Channels	1
Number of Bits	14
Number of Functions	1
Number of Terminals	28
Operating Temperature-Min	0.0 Cel
Operating Temperature-Max	70.0 Cel
Output Bit Code	2'S COMPLEMENT BINARY
Output Format	PARALLEL, WORD
Package Body Material	PLASTIC/EPOXY
Package Code	SSOP
Package Equivalence Code	SSOP28,.3
Package Shape	RECTANGULAR
Package Style	SMALL OUTLINE, SHRINK PITCH
Peak Reflow Temperature (Cel)	235
Power Supplies (V)	+5
Qualification Status	Not Qualified
Sample-and-Hold/Track-and-Hold	SAMPLE
Serial Rate	0.8 Mbit/s

### Temperature

25

### Voltage

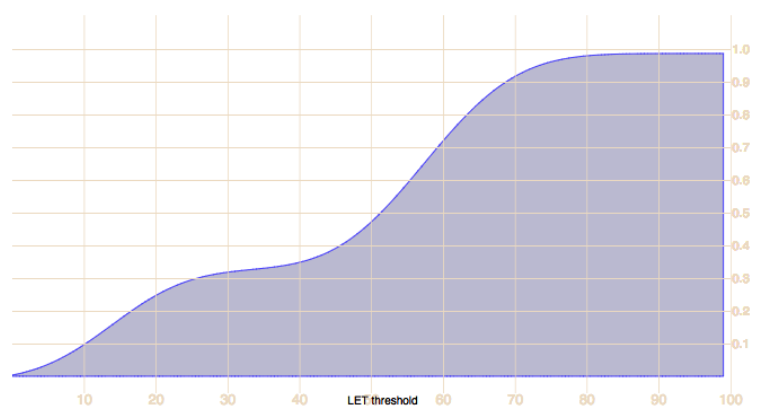
3

Update

### Test Info

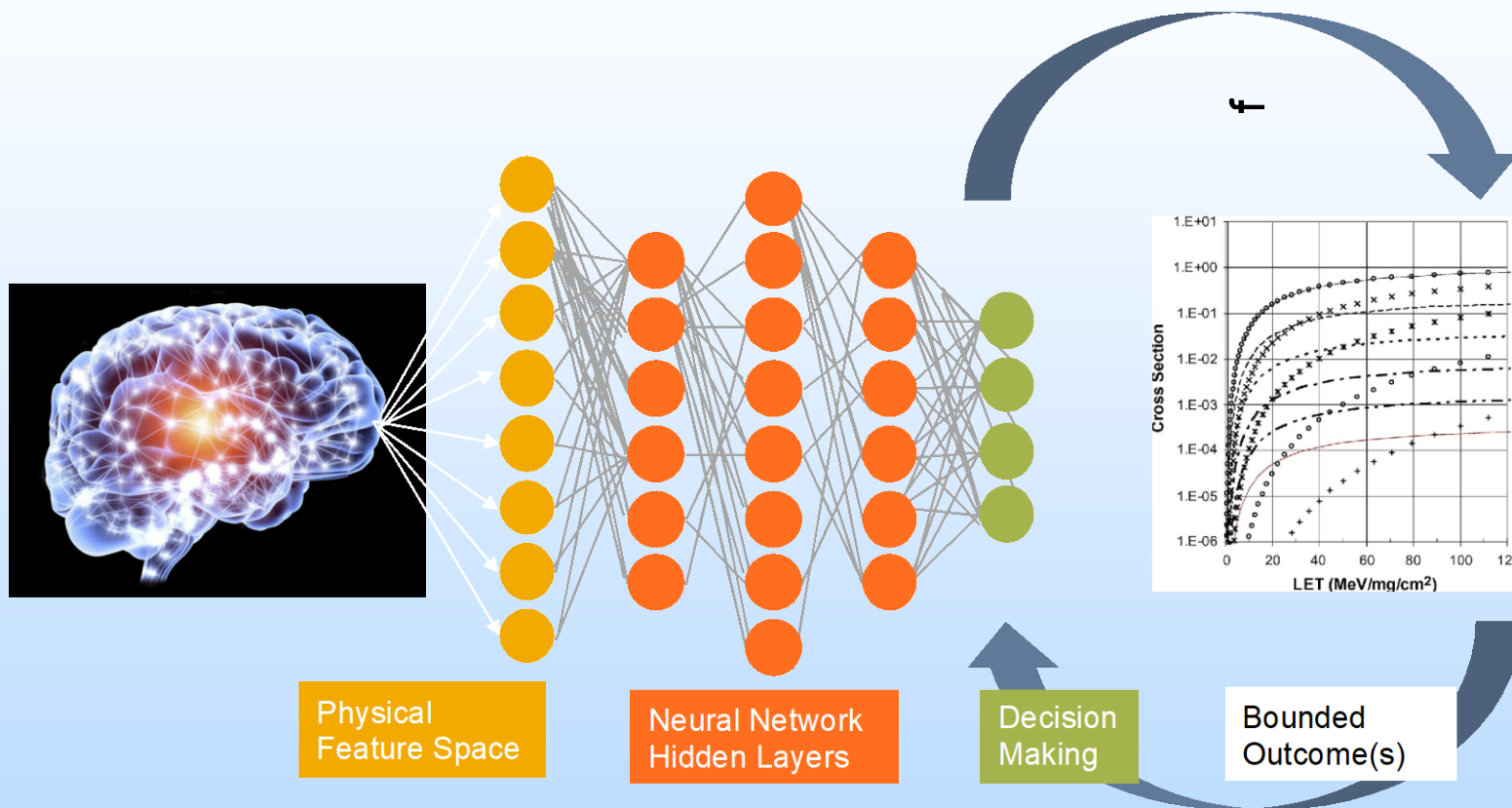
Part	Temperature	Voltage	Details
LTC1419			64.0 < SEL < 68.3

### Risk Threshold





# Metadata Analysis





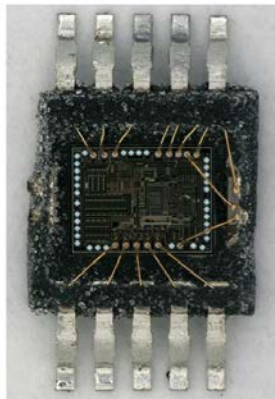


# Automatic Semantic Segmentation of Radiation Susceptible Electronics

- We attempt to built an automated system that can take the input of electronic die data and output the amount of susceptible area.
- The idea is that the greater the area of underlying components such as those that are CMOS is nature, is proportional to the susceptibility of the component undergoing various radiation effects

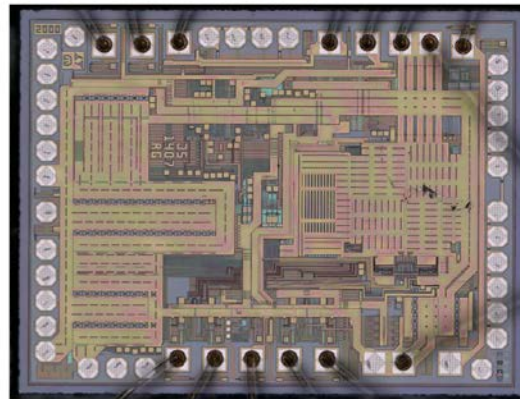
Plasma Etch of Linear Tech LTC1272-8CCSW#PBF

Post Wet Etch



Optical image showing the complete exposed die.

Post Wet Etch



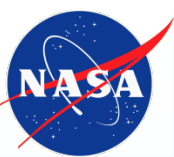
Optical image showing a detailed view of the die. Scratch in the die is an artifact from handling.





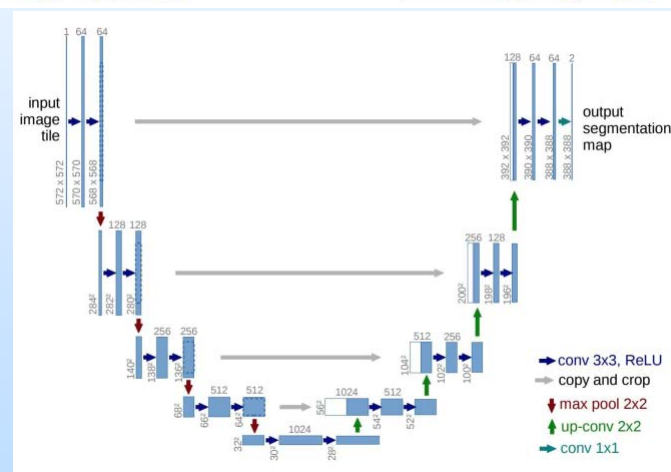
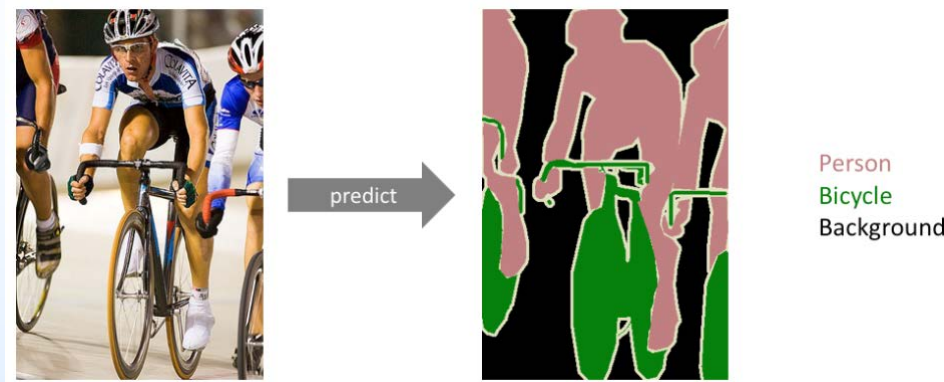
# Methodology

- **Data Collection**
  - Electronic dies are consistently being made
- **Labeling**
  - Labeling of the the electronic dies with the radiation susceptible areas vs. non radiation susceptible areas is a time consuming process. We label these images by drawing multiple bounding boxes on top of the die images so that we can generate 'masks' of areas of prediction
- **Semantic Segmentation**
  - We then build computer vision models that attempt to predict the class of every pixel on the die image one by one to determine total susceptibility of an electronic part



# Semantic Segmentation

- Goal is to take raw pixels + pixel labels to predict the classes of the pixels
- There are many popular methods for accomplishing this task, some of which include
  - Fully Convolutional Models
  - Encoder – Decoder Models
  - Pyramid Based Network Models
  - R-CNN Based Models
  - DeepLab Based Models
  - Etc.



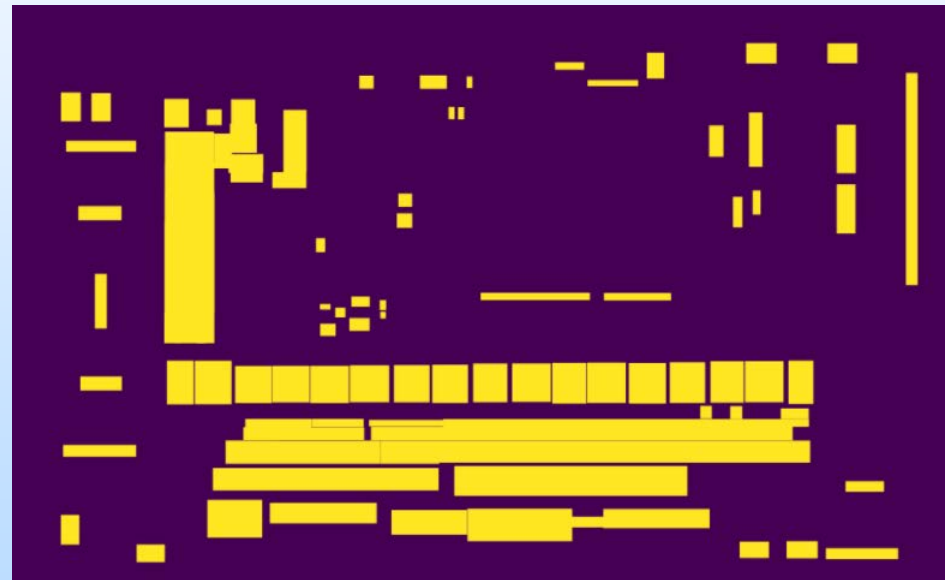
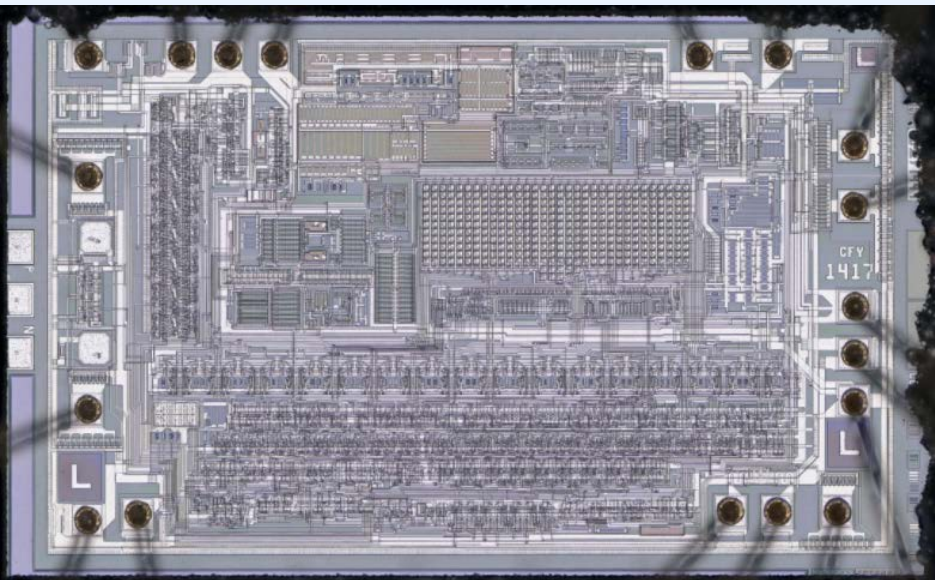
– Example U-Net architecture that falls into the ‘Encoder-Decoder Models’ family



# High Image Resolution

## Example Die Image and Mask (LTC1417)

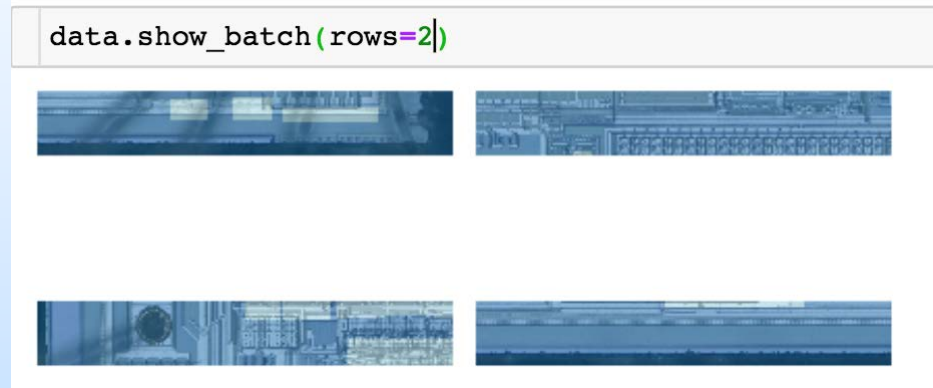
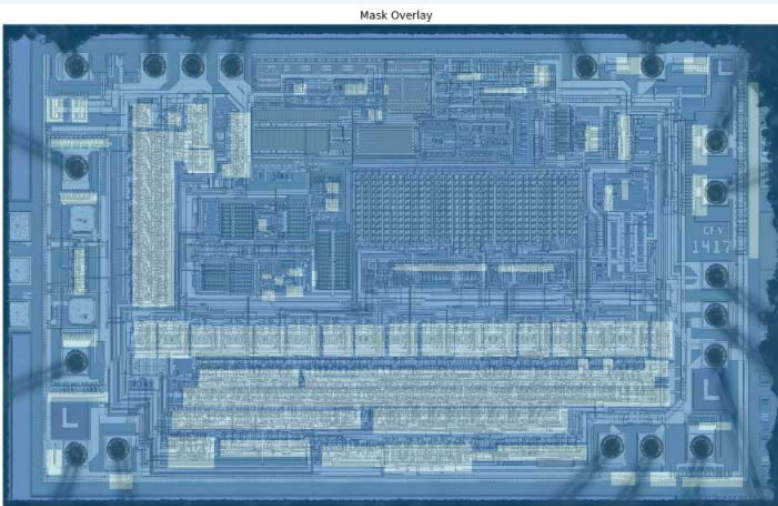
- Challenge of needing to properly splice the high resolution images into appropriate tiles to train, and then assemble back together





# Showing the Mask Overlay

## Into Tile Transformation





# Conclusions & Future Work

- Continue to develop machine learning methodologies
- Repeat with spatially correlated SEL data from pulse laser
- Repeat with “fuller” database

